STTH2003C-Y



Automotive high efficiency ultrafast diode

Datasheet - production data

Features

- High junction temperature
- Combines highest recovery and reverse voltage performance
- Ultrafast, soft and noise-free recovery
- AEC-Q101 qualified

Description

This dual center tap rectifier is suited for switch mode power supplies and high frequency DC to DC converters.

Packaged in D²PAK, this device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection for automotive applications.

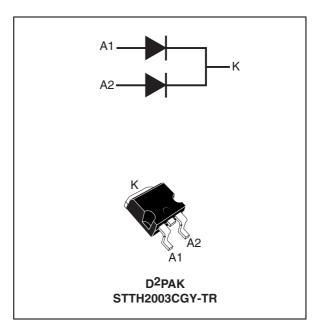


Table 1. Device summary

I _F (AV)	2 x 10 A
V _{RRM}	300 V
T _j (max)	175 °C
V _F (max)	1 V
t _{rr} (max)	40 ns

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1 Characteristics

Table 2. Absolute ratings (limiting values, per diode)

Symbol	Paramete	Value	Unit		
V_{RRM}	Repetitive peak reverse voltage				V
I _{F(RMS)}	Forward current rms	48	Α		
I _{F(AV)}	Average forward current, $\delta = 0.5$ $T_c = 140 ^{\circ}\text{C}$ Per diode Per device		10 20	Α	
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal } (T_j = 25 ^{\circ}\text{C})$			110	Α
T _{stg}	Storage temperature range	-65 to + 175	Ô		
T _j	Operating junction temperature range				°C

Table 3. Thermal resistance

Symbol	Parameter	Value (Max.)	Unit	
В	Junction to case	Per diode	2.5	°C/W
□th(j-c)	Junction to case	Total	1.3	°C/VV

Table 4. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
I _B ⁽¹⁾	Poverce leakage current	T _j = 25 °C	V _R = 300 V			20	μA
I _R ⁽¹⁾ Reverse leakage current	T _j = 125 °C	v _R = 300 v		30	300	μΛ	
V _F ⁽²⁾ Forward voltage drop	T _j = 25 °C	I _F = 10 A			1.25	V	
	Forward voltage drop	T _j = 125 °C	1 _F = 10 A		0.85	1	V

^{1.} Pulse test: $t_p = 5 \text{ ms}$, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

$$P = 0.75 \text{ x } I_{F(AV)} + 0.025 I_{F}^{2}_{(RMS))}$$

^{2.} Pulse test: t_p = 380 μ s, δ < 2%

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Table 5. Recovery characteristics

Symbol	Parameter	Test conditions		Min.	Тур.	Max.	Unit
	Poverse recovery time	T _i = 25 °C	$I_F = 0.5 \text{ A}, I_{rr} = 0.25 \text{ A}$ $I_R = 1 \text{ A}$			25	20
t _{rr}	Reverse recovery time	1 _j = 25 C	$I_F = 1 \text{ A}, V_R = 30 \text{ V}$ $dI_F/dt = -50 \text{ A}/\mu\text{s}$			40	ns
t _{fr}	Forward recovery time	T _j = 25 °C	$I_F = 10 \text{ A}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}$			230	ns
V _{FP}	Peak forward voltage	T _j = 25 °C	$I_F = 10 \text{ A},$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$			3.5	٧
I _{RM}	Reverse recovery current	T _i = 125 °C	$I_{\rm F} = 10 \text{A}, V_{\rm CC} = 200 \text{V}$			8	Α
S factor	Softness factor	$dI_F/dt = 200 \text{ A/}\mu\text{s}$			0.3		-

Figure 1. Conduction losses versus average Figure 2. forward current (per diode)

Forward voltage drop versus forward current (maximum values, per diode)

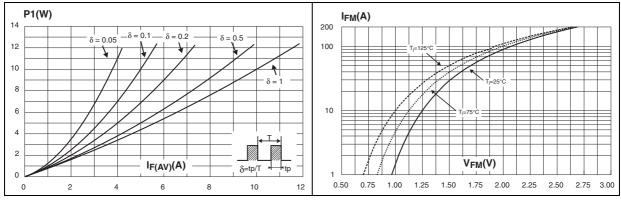
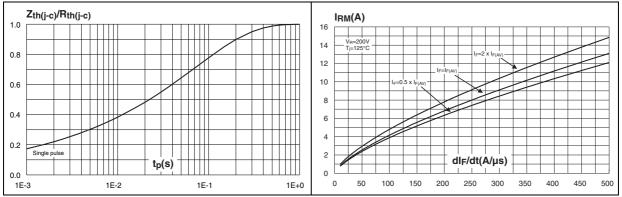


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (90% confidence, per diode)



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Figure 5. Reverse recovery time versus dI_F/dt Figure 6. Softness factor (tb/ta) versus dI_F/dt (typical values, per diode)

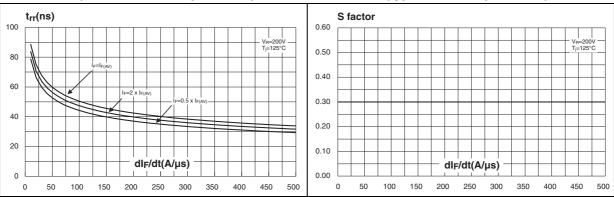


Figure 7. Relative variation of dynamic parameters versus junction temperature (reference: $T_i = 125$ °C)

Figure 8. Forward recovery time versus dl_F/dt (90% confidence, per diode)

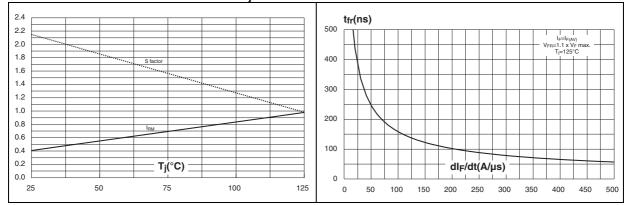
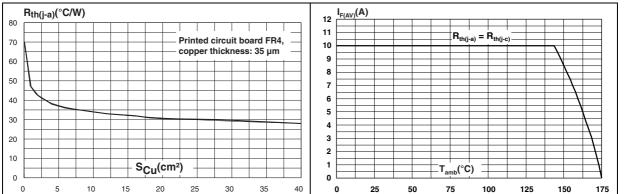


Figure 9. Thermal resistance, junction to ambient, versus copper surface under tab

Figure 10. Average forward current versus ambient temperature (δ = 0.5, per diode)



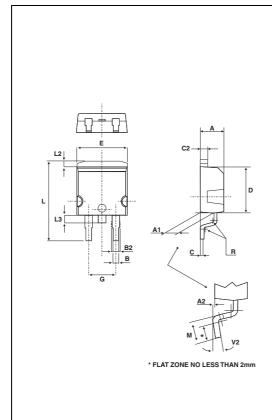
STTH2003C-Y Package information

2 Package information

- Epoxy meets UL94, V0
- Cooling method: by conduction (C)

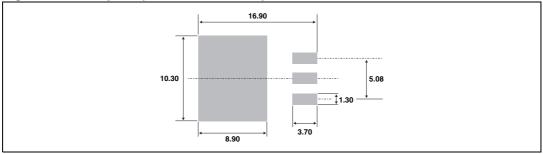
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Table 6. D²PAK dimensions



	Dimensions				
Ref.	. Millimeters		Inc	hes	
	Min.	Max.	Min.	Max.	
Α	4.40	4.60	0.173	0.181	
A1	2.49	2.69	0.098	0.106	
A2	0.03	0.23	0.001	0.009	
В	0.70	0.93	0.027	0.037	
B2	1.14	1.70	0.045	0.067	
С	0.45	0.60	0.017	0.024	
C2	1.23	1.36	0.048	0.054	
D	8.95	9.35	0.352	0.368	
Е	10.00	10.40	0.393	0.409	
G	4.88	5.28	0.192	0.208	
L	15.00	15.85	0.590	0.624	
L2	1.27	1.40	0.050	0.055	
L3	1.40	1.75	0.055	0.069	
М	2.40	3.20	0.094	0.126	
R	0.40	typ.	0.016 typ.		
V2	0°	8°	0°	8°	

Figure 11. Footprint (dimensions in mm)



Ordering information STTH2003C-Y

3 Ordering information

Table 7. Ordering information

Order code	Marking	Package	Weight	Base qty	Delivery mode
STTH2003CGY-TR	STTH2003CGY	D ² PAK	1.48 g	1000	Tape and reel

4 Revision history

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Table 8. Document revision history

Date	Revision	Changes
24-Oct-2012	1	Initial release.

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